

INFORMATION DISCLOSURE CITATION FORM FOR PATENT APPLICATION (FORM PTO-1449) (Substitute)			Docket No.: Y0R920030208US1	Serial No.:		
			Applicant(s): Hyungjun KIM et al.			
			Filing Date:	Group:		
U.S. PATENTS						
Initials	Patent Number	Issue Date	Name	Class	Sub-class	Filing date
FOREIGN PATENT DOCUMENTS						
Initials	Document Number	Date	Country	Name		Translation? Yes/No/n/a
OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)						
BC	Kim et al., Diffusion barrier properties of transition metal thin films grown by plasma-enhanced atomic layer deposition, J. Vac. Sci. Technol. B 20(4), J/A 2002					
	Kim et al., Growth kinetics and initial stage growth during plasma-enhanced Ti atomic layer deposition, J. Vac. Sci. Technol. A 20(3), May/June 2002					
	Rossnagel et al., Plasma-enhanced atomic layer deposition of Ta and Ti for inter-connect diffusion barriers, J. Vac. Sci. Technol. B 18(4), July/Aug 2002					
Examiner's Signature: /Bret Chen/				Date Considered: 05/26/2006		
Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).						

**INFORMATION DISCLOSURE
STATEMENT BY THIRD-PARTY**

(Multiple sheets used when necessary)

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SHEET 1 OF 1

Application No.	10/699,226
Filing Date	October 31, 2003
First Named Inventor	Kim
Art Unit	1775
Examiner	Turner, Archene A.
Attorney Docket No.	

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
BC		2004/0009307 A1	01-15-2004	Koh et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
BC		Atomic Layer Deposition (ALD) 2002 American Vacuum Society Topical Conference, August 19-21, 2002, Hanyang University, Korea, Program Schedule and Content.	
		H. KIM & S.M. ROSSNAGEL, "The Growth and Properties of PE-ALD Ta and TaN Thin Films" (Invited lecture), Atomic Layer Deposition (ALD) 2002 American Vacuum Society Topical Conference, August 19-21, 2002, Hanyang University, Korea, Abstract.	
BC		H. KIM & S.M. ROSSNAGEL, "The Growth and Properties of PE-ALD Ta and TaN Thin Films" (Invited lecture), Atomic Layer Deposition (ALD) 2002 American Vacuum Society Topical Conference, August 19-21, 2002, Hanyang University, Korea, Presentation Slides.	

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Examiner Signature	/Bret Chen/	Date Considered	05/26/2006
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

T¹ - Place a check mark in this area when an English language Translation is attached.